Notice of References Cited

Application/Control No.

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Examiner

Fernando Toledo

Applicant(s)/Patent Under
Reexamination
ISHIDA ET AL.

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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,508,911 B1	01-2003	Han et al.	118/7231
	В	US-6,230,400 B1	05-2001	Tzanavaras et al.	29/840
	C	US-6,120,640 A	09-2000	Shih et al.	156/345.1
	D	US-5,434,104 A	07-1995	Cain et al.	438/652
	E	US-5,238,872 A	08-1993	Thalapaneni, Gurunada	438/453
	F	US-6,537,925 B2	03-2003	Kim et al.	438/758
	G	US-6,281,147 B1	08-2001	Yamazaki et al.	438/788
	н	US-6,274,514 B1	08-2001	Jang et al.	438/778
	1	US-6,133,162 A	10-2000	Suzuki et al.	438/780
	J	US-6,037,274 A	03-2000	Kudo et al.	438/778
	к	US-6,071,830 A	06-2000	Matsuzawa et al.	438/778
	Ļ	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	s					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)		
	U	Ghandhi, Sorab; VLSI Fabrication Principles Silicon and Gallium Arsenide, Second Ed., Jhon Wiley & Sons, Inc. page 641		
	V	Merriam Webster's Collegiate Dictionary 10th Edition, Merrian Webster Inc. page 254		
	w			
	х			

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.